



**THE DATASHEET OF  
NRVBB41H100CTT4G**



# Switch-mode Power Rectifier 100 V, 40 A

## MBR41H100CT, NRVBB41H100CT Series

### Features and Benefits

- Low Forward Voltage: 0.67 V @ 125°C
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 40 A Total (20 A Per Diode Leg)
- Guard-Ring for Stress Protection
- NRVBB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant
- MBR41H100CTH and MBRB41H100CT-1H are Halide-Free

### Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

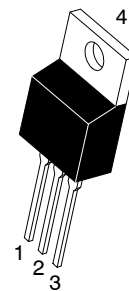
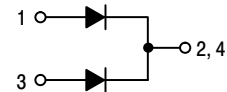
### Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220)  
1.7 Grams (D<sup>2</sup>PAK-3)  
1.5 Grams (TO-262)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes:  
260°C Max. for 10 Seconds



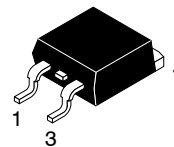
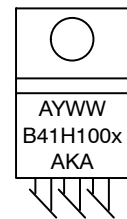
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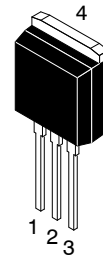
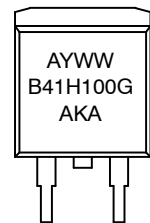


TO-220  
CASE 221A  
STYLE 6

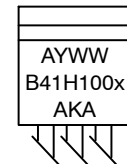
### MARKING DIAGRAMS



D<sup>2</sup>PAK-3  
CASE 418B  
STYLE 3



I<sup>2</sup>PAK (TO-262)  
CASE 418D  
STYLE 3



A = Assembly Location  
Y = Year  
WW = Work Week  
x = G or H  
G = Pb-Free Package  
H = Halide-Free Package  
AKA = Polarity Designator

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

## MBR41H100CT, NRVBB41H100CT Series

### MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current (Rated $V_R$ ) $T_C = 150^\circ\text{C}$	$I_{F(AV)}$	20	A
Peak Repetitive Forward Current (Rated $V_R$ , Square Wave, 20 kHz) $T_C = 145^\circ\text{C}$	$I_{FRM}$	40	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	$I_{FSM}$	350	A
Operating Junction Temperature (Note 1)	$T_J$	+175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Voltage Rate of Change (Rated $V_R$ )	dv/dt	10,000	V/ $\mu\text{s}$
Controlled Avalanche Energy (see test conditions in Figures 10 and 11)	$W_{AVAIL}$	400	mJ
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient:  $dP_D/dT_J < 1/R_{\theta JA}$ .

### THERMAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.0 70	$^\circ\text{C}/\text{W}$

### ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Value	Unit
Maximum Instantaneous Forward Voltage (Note 2) ( $I_F = 20\text{ A}$ , $T_C = 25^\circ\text{C}$ ) ( $I_F = 20\text{ A}$ , $T_C = 125^\circ\text{C}$ ) ( $I_F = 40\text{ A}$ , $T_C = 25^\circ\text{C}$ ) ( $I_F = 40\text{ A}$ , $T_C = 125^\circ\text{C}$ )	$V_F$	0.80 0.67 0.90 0.76	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 125^\circ\text{C}$ ) (Rated DC Voltage, $T_C = 25^\circ\text{C}$ )	$i_R$	10 0.01	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

# MBR41H100CT, NRVBB41H100CT Series

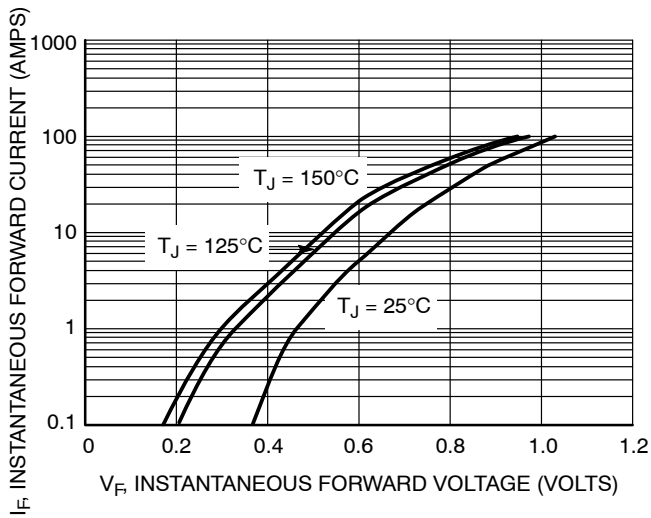


Figure 1. Typical Forward Voltage

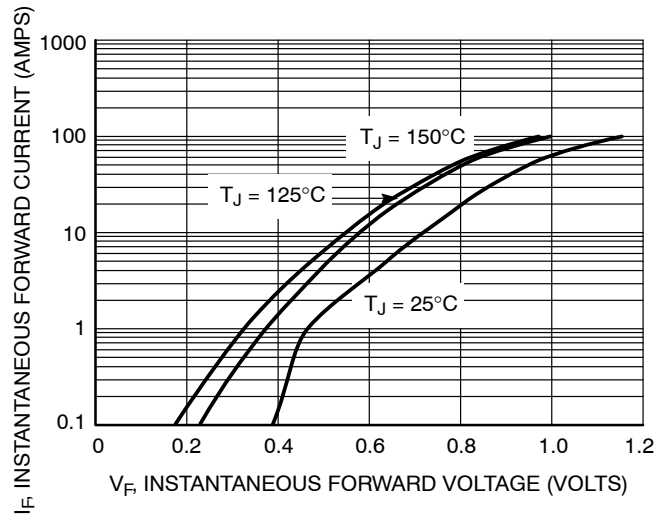


Figure 2. Maximum Forward Voltage

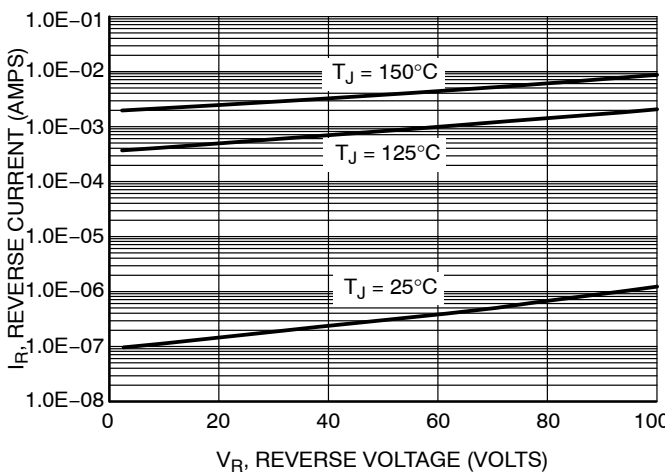


Figure 3. Typical Reverse Current

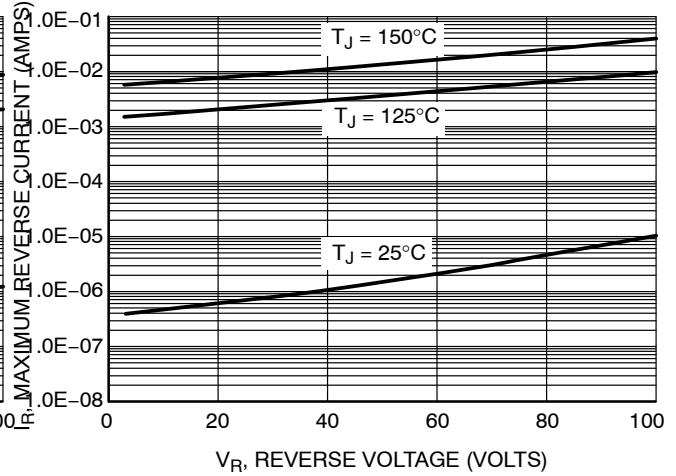


Figure 4. Maximum Reverse Current

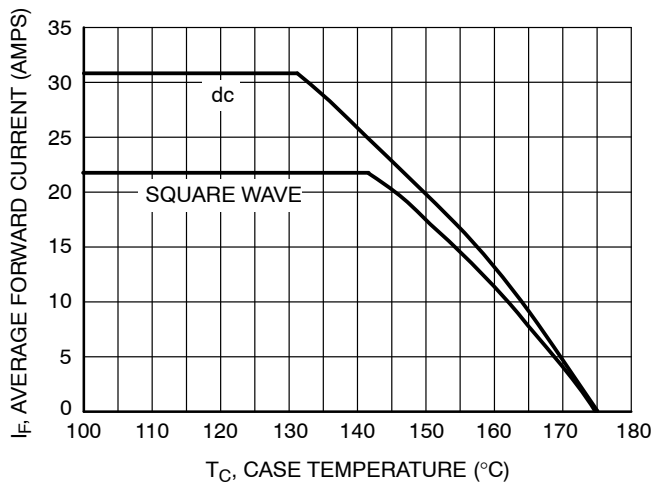


Figure 5. Current Derating

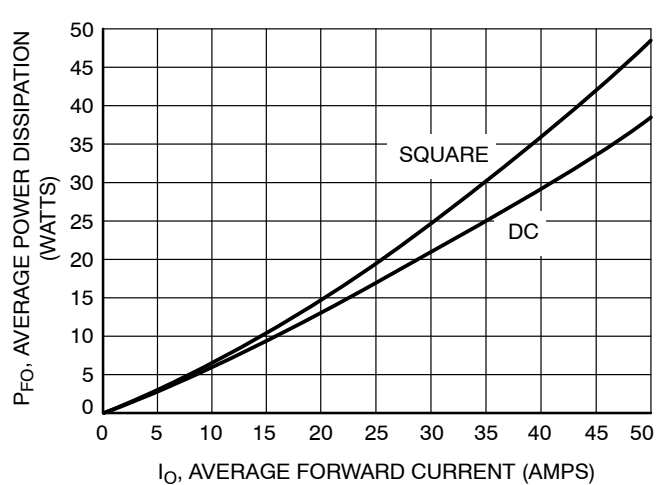


Figure 6. Forward Power Dissipation

# MBR41H100CT, NRVBB41H100CT Series

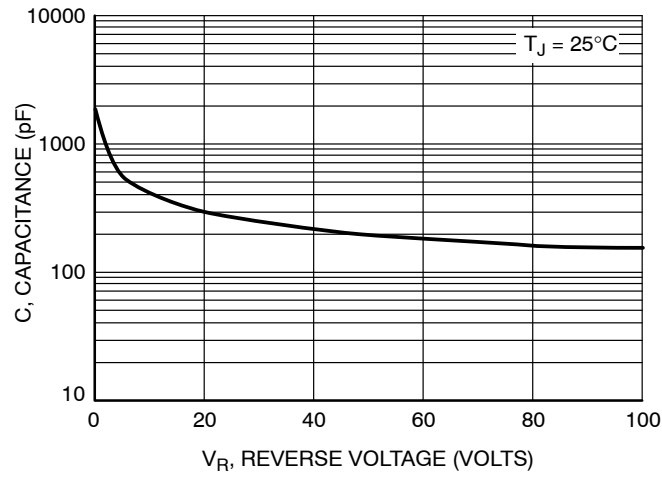


Figure 7. Capacitance

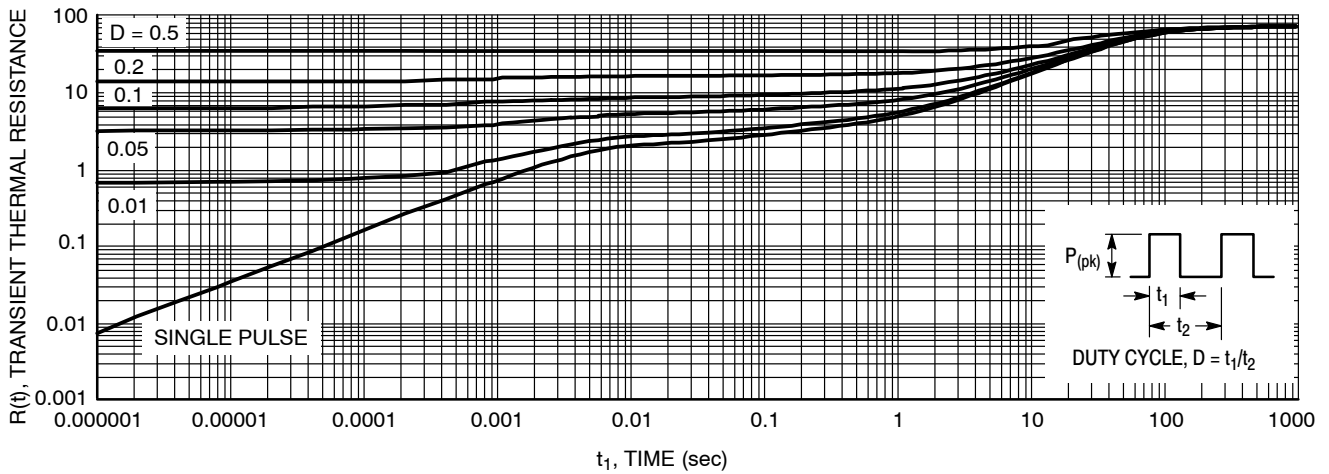


Figure 8. Thermal Response Junction-to-Ambient

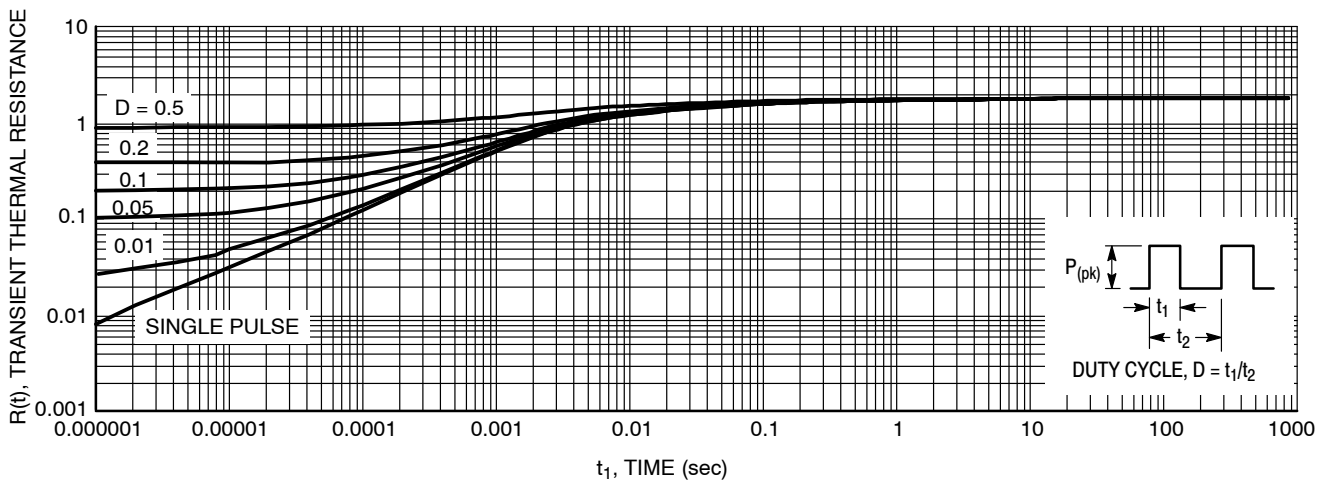
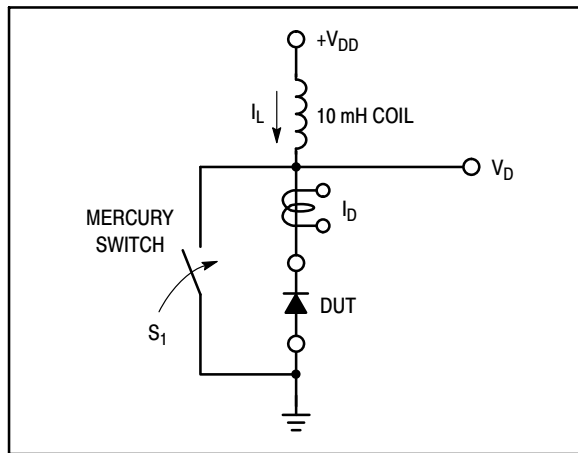


Figure 9. Thermal Response Junction-to-Case

## MBR41H100CT, NRVBB41H100CT Series

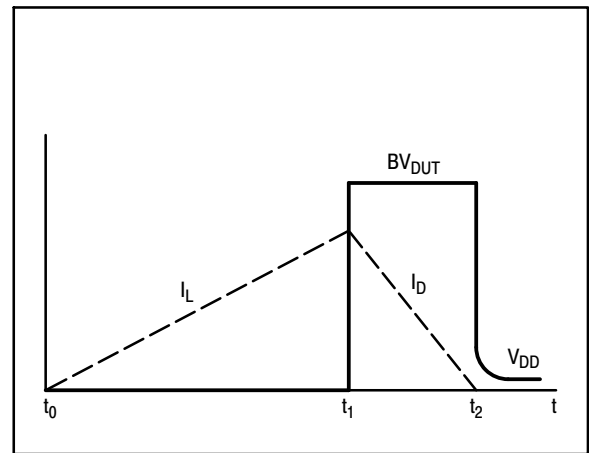


**Figure 10. Test Circuit**

The unclamped inductive switching circuit shown in Figure 10 was used to demonstrate the controlled avalanche capability of this device. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When  $S_1$  is closed at  $t_0$  the current in the inductor  $I_L$  ramps up linearly; and energy is stored in the coil. At  $t_1$  the switch is opened and the voltage across the diode under test begins to rise rapidly, due to  $di/dt$  effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at  $BV_{DUT}$  and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at  $t_2$ .

By solving the loop equation at the point in time when  $S_1$  is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the  $V_{DD}$  power supply while the diode is in breakdown (from  $t_1$  to  $t_2$ ) minus any losses due to finite component resistances. Assuming the component resistive



**Figure 11. Current-Voltage Waveforms**

elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the  $V_{DD}$  voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when  $S_1$  was closed, Equation (2).

**EQUATION (1):**

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2 \left( \frac{BV_{DUT}}{BV_{DUT} V_{DD}} \right)$$

**EQUATION (2):**

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2$$

## MBR41H100CT, NRVBB41H100CT Series

### ORDERING INFORMATION

Device	Package	Shipping†
MBR41H100CTG	TO-220 (Pb-Free)	50 Units / Rail
MBR41H100CTH	TO-220 (Halide-Free)	50 Units / Rail
MBRB41H100CT-1G	I <sup>2</sup> PAK (Pb-Free)	50 Units / Rail
MBRB41H100CT-1H (In Development)	I <sup>2</sup> PAK (Halide-Free)	50 Units / Rail
MBRB41H100CTT4G	D <sup>2</sup> PAK 3 (Pb-Free)	800 Units / Tape & Reel
NRVBB41H100CTT4G*	D <sup>2</sup> PAK 3 (Pb-Free)	800 Units / Tape & Reel

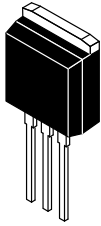
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NRVBB Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

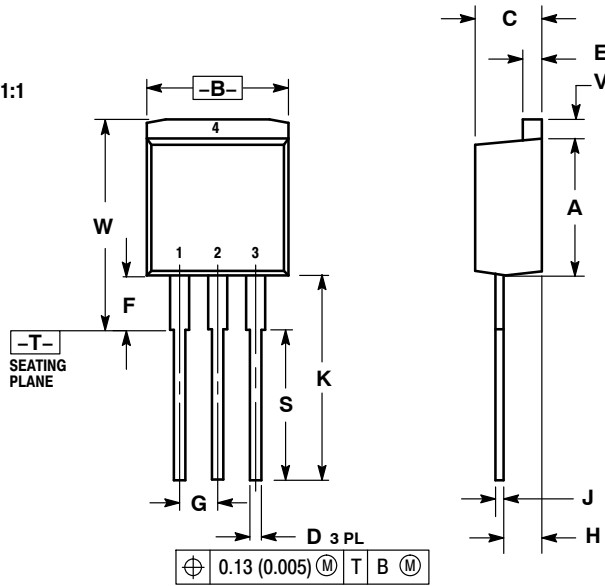
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SCALE 1:1

I<sup>2</sup>PAK (TO-262)  
CASE 418D-01  
ISSUE D

DATE 16 OCT 2007



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.335	0.380	8.51	9.65
B	0.380	0.406	9.65	10.31
C	0.160	0.185	4.06	4.70
D	0.026	0.035	0.66	0.89
E	0.045	0.055	1.14	1.40
F	0.122 REF		3.10 REF	
G	0.100 BSC		2.54 BSC	
H	0.094	0.110	2.39	2.79
J	0.013	0.025	0.33	0.64
K	0.500	0.562	12.70	14.27
S	0.390 REF		9.90 REF	
V	0.045	0.070	1.14	1.78
W	0.522	0.551	13.25	14.00

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

STYLE 3:

1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

STYLE 4:

1. GATE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

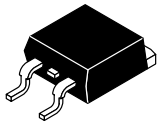
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# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

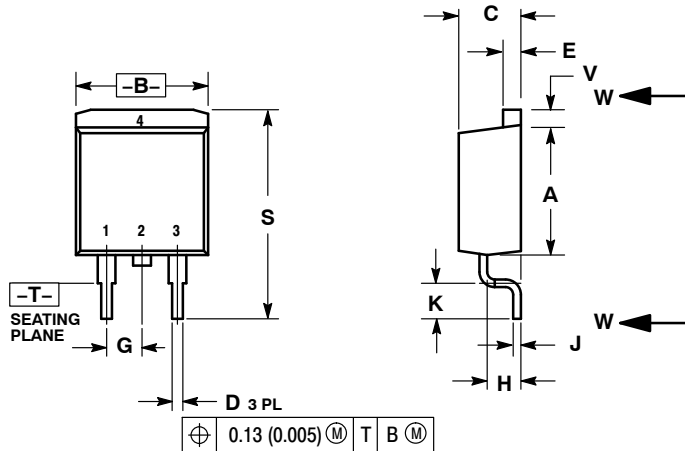
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**D<sup>2</sup>PAK 3**  
CASE 418B-04  
ISSUE L

DATE 17 FEB 2015

SCALE 1:1

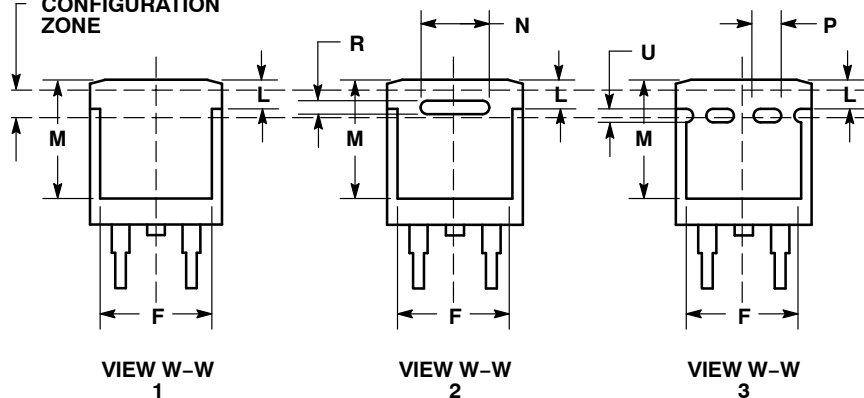


**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100	BSC	2.54	BSC
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197	REF	5.00	REF
P	0.079	REF	2.00	REF
R	0.039	REF	0.99	REF
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

**VARIABLE CONFIGURATION ZONE**



- |  |   |   |  |   |  |
|--|---|---|--|---|--|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN | <b>STYLE 3:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. ANODE<br>4. CATHODE | <b>STYLE 4:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 5:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. CATHODE<br>4. ANODE | <b>STYLE 6:</b><br>PIN 1. NO CONNECT<br>2. CATHODE<br>3. ANODE<br>4. CATHODE |
|--|---|---|--|---|--|

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